BR1005 THRU BR1010

SINGLE PHASE SILICON BRIDGE RECTIFIERS

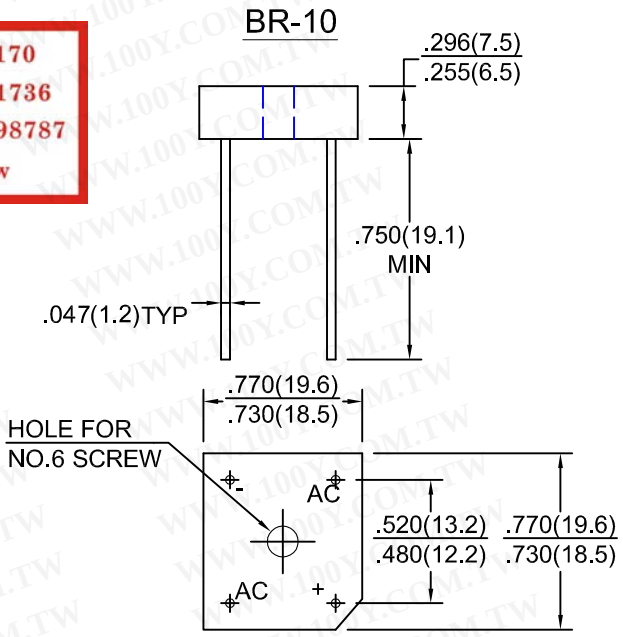
勝 特 力 材 料 886-3-5753170
胜特力电子(上海) 86-21-54151736
胜特力电子(深圳) 86-755-83298787
Http://www.100y.com.tw

FEATURES:

- Low forward voltage drop
- Low leakage current

MECHANICAL DATA

Case : Molded plastic body
Polarity : marked on body
Mounting position : Any
Mounting : Hole thru for # 6 screw



Dimensions in inches and (millimeters)

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating at 25℃ ambient temp. unless otherwise specified.
Single phase, half sine wave, 60 Hz, resistive or inductive load.
For capacitive load, derate current by 20 %.

Characteristic	Symbol	BR 1005	BR 101	BR 102	BR 104	BR 106	BR 108	BR 1010	Units
Maximum recurrent peak reverse voltage	V_{RRM}	50	100	200	400	600	800	1000	Volts
Maximum RMS voltage	V_{RMS}	35	70	140	280	420	560	700	Volts
Maximum DC blocking voltage	V_{DC}	50	100	200	400	600	800	1000	Volts
Maximum average forward rectified current .375"(9.5mm) lead length at Tc=50℃	I_O	10							Amps
Peak forward surge current ,8.3ms single half sine-wave superimposed on rated load(JEDEC Method)	I_{FSM}	150							Amps
Maximum instantaneous forward voltage drop per bridge element at 5.0 A DC	V_F	1.1							Volts
Maximum DC reverse current Ta=25℃ / at rated DC blocking voltage Ta=100℃	I_R	10 / 1000							μA
Typical junction capacitance	C_j	55							pF
Typical thermal resistance	R_{th}-JA	9.4							℃/W
Operating temperature range	T_j	-65 to +150							℃
Storage temperature range	T_{stg}	-65 to +150							℃

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FIG.1-TYPICAL FORWARD CURRENT DERATING CURVE

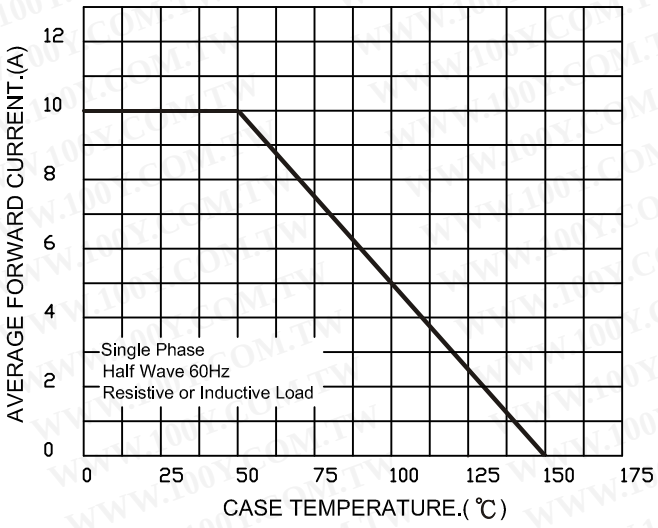


FIG.2-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

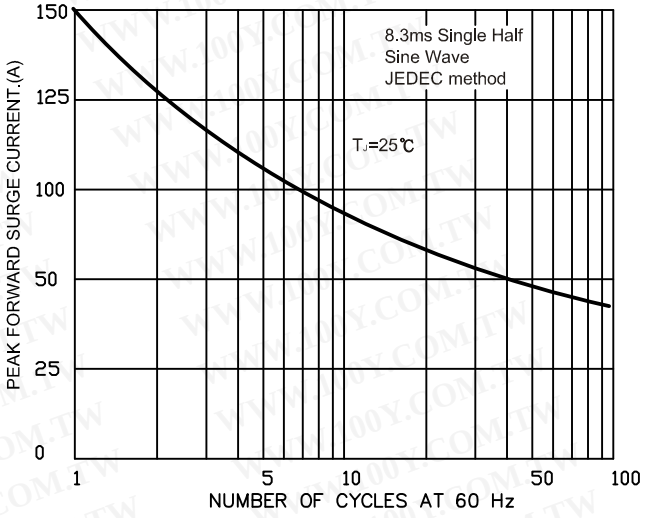


FIG.3-TYPICAL FORWARD CHARACTERISTICS

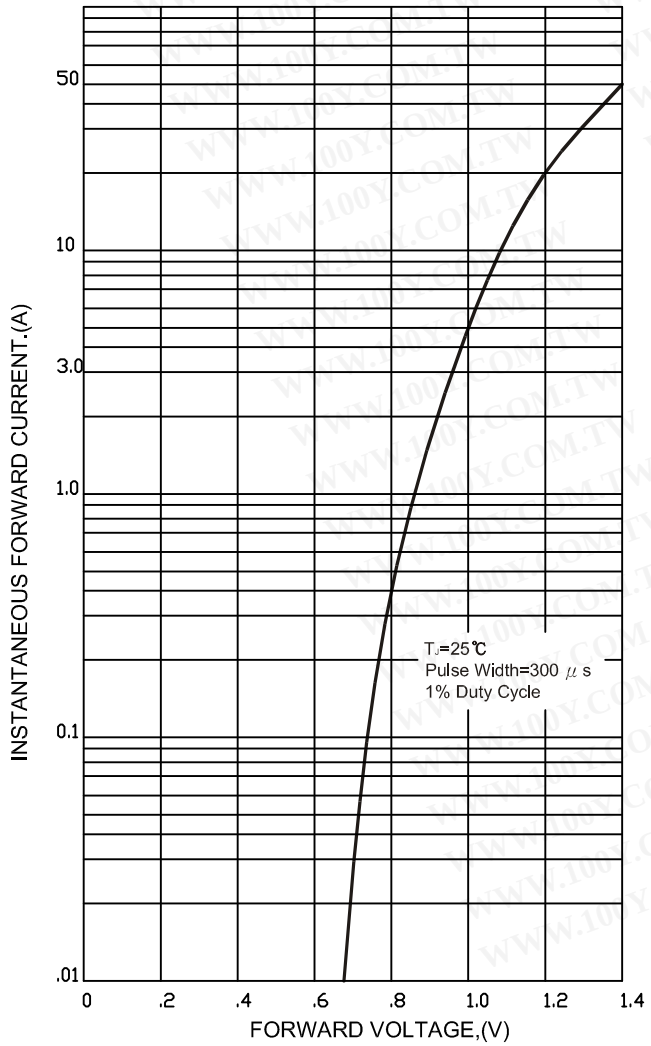
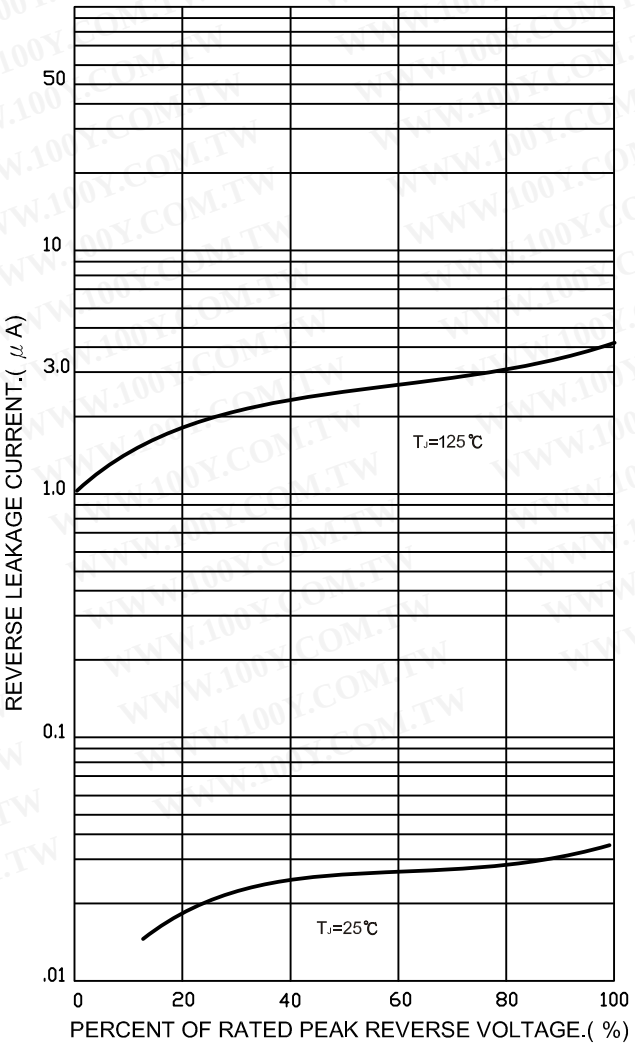


FIG.4-TYPICAL REVERSE CHARACTERISTICS



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